
	No.1396	2SC3481 NPN Triple Diffused Planar Type Silicon Transistor FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL DEFLECTION OUTPUT APPLICATIONS (BUILT-IN DAMPER DIODE)
		

Features:

- High breakdown voltage and high reliability
- High switching speed: $t_f=0.3\mu s$ max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

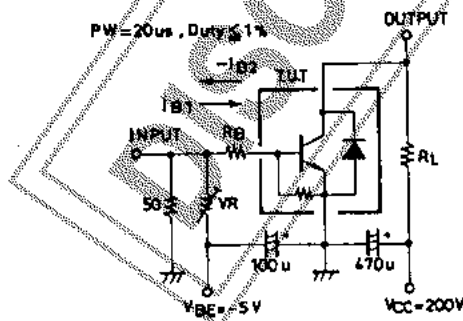
Absolute Maximum Ratings at $T_a=25^\circ C$

			unit
Collector to Base Voltage	VCBO	1500	V
Collector to Emitter Voltage	VCEO	800	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	5	A
Peak Collector Current	icp	16	A
Collector Dissipation	PC	$T_c=25^\circ C$	120 W
Junction Temperature	Tj	150	$^\circ C$
Storage Temperature	Tstg	-55 to +150	$^\circ C$

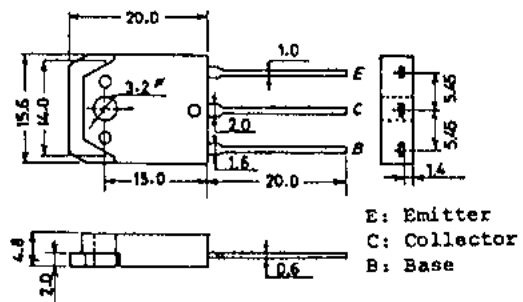
Electrical Characteristics at $T_a=25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	ICBO	VCB=800V, IE=0			10	μA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0	40		130	mA
DC Current Gain	hFE	VCE=5V, IC=1A	8			
Gain Bandwidth Product	ft	VCE=10V, IC=1A		3		MHz
C-E Saturation Voltage	VCE(sat)	IC=4A, IB=1A			5	V
B-E Saturation Voltage	VBE(sat)	IC=4A, IB=1A			1.5	V
C-B Breakdown Voltage	V(BR)CBO	IC=5mA, IE=0	1500			V
C-E Breakdown Voltage	V(BR)CEO	IC=5mA, RE=∞	800			V
E-B Breakdown Voltage	V(BR)EBO	IE=200mA, IC=0	7			V
Diode Forward Voltage	Vf	IEC=5A			2	V
Storage Time	tstg	$\left[\begin{array}{l} IC=4A, IB1=0.8A, \\ IB2=-1.6A, VCC=200V, \\ RL=50ohm \end{array} \right]$			3.0	μs
Fall Time	tf				0.3	μs

Switching Time Test Circuit

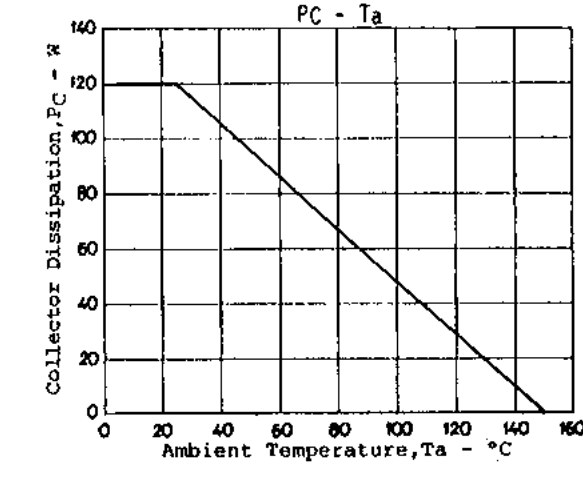
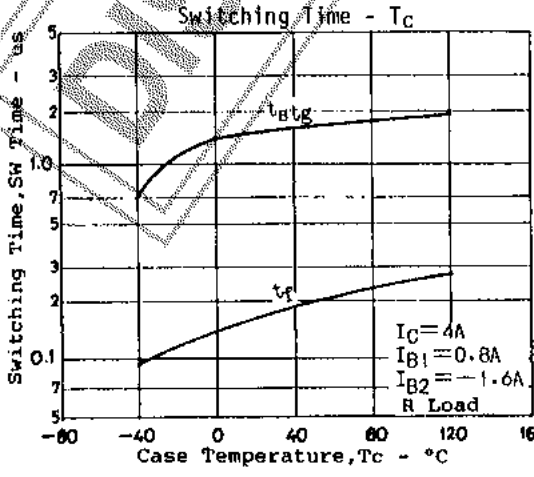
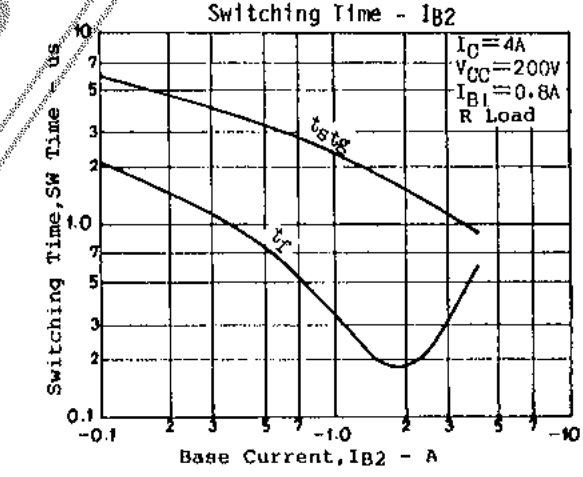
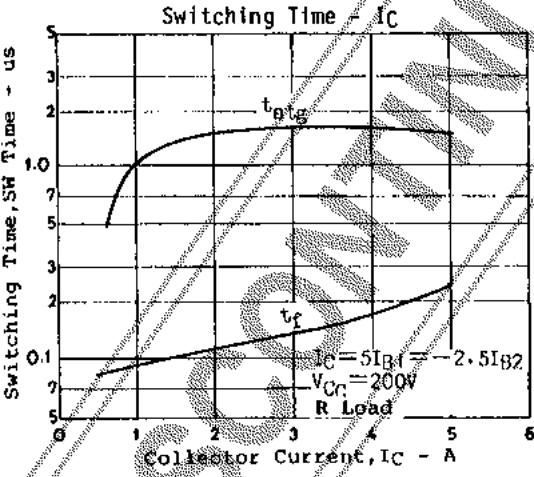
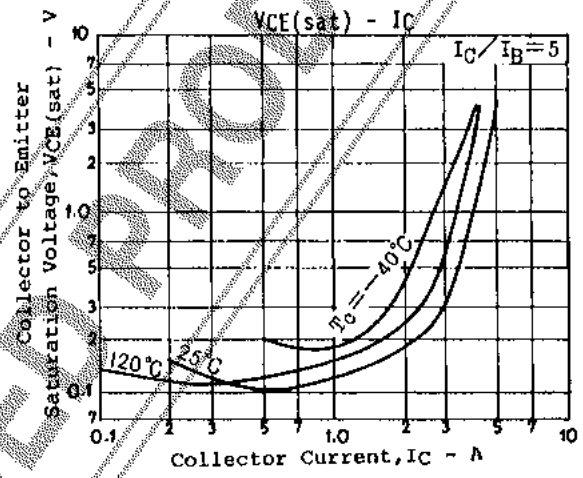
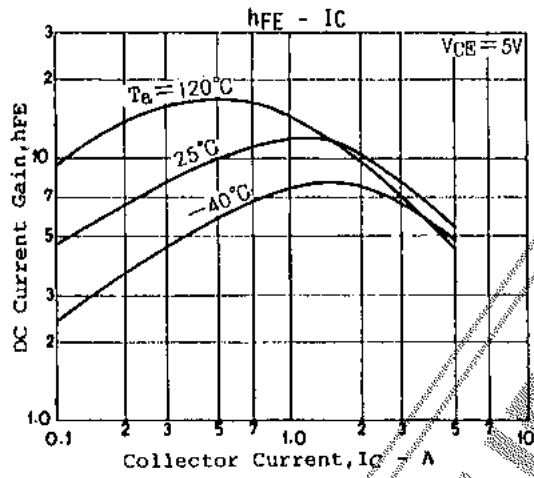
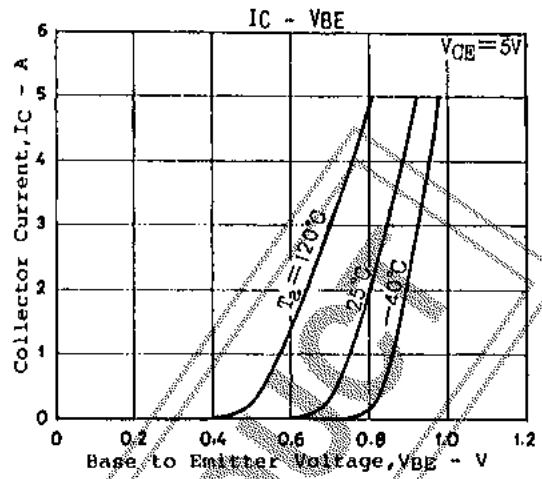
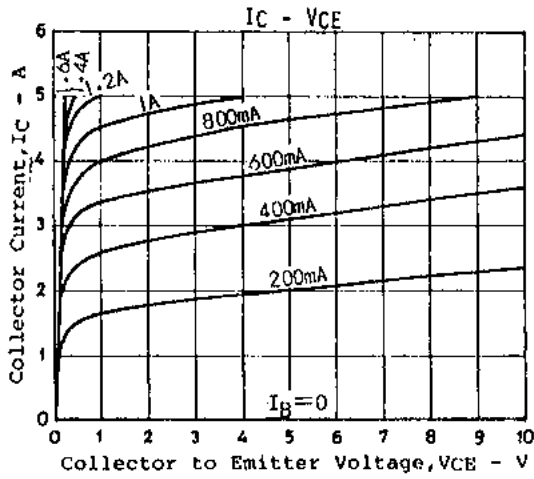


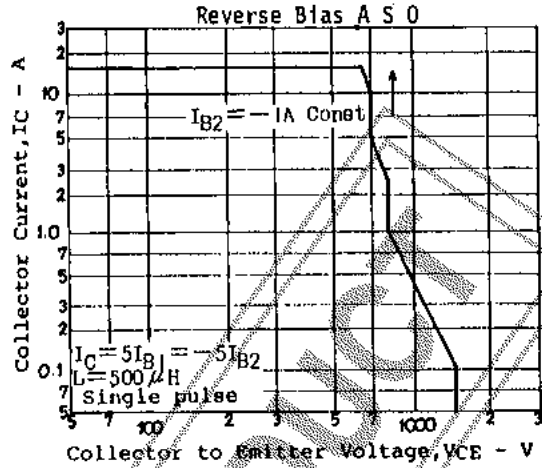
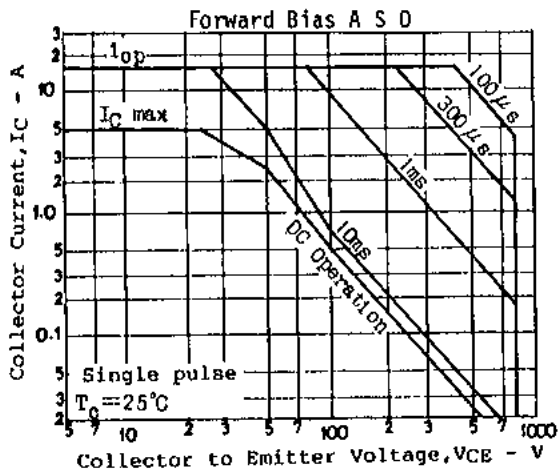
Case Outline 2022 (unit:mm)



These specifications are subject to change without notice.

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